

### **Description**

The BSS816NWH6327XTSA1 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.



**SOT-323** 

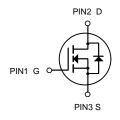
#### **General Features**

 $V_{DS} = 20V I_{D} = 2A$ 

 $R_{DS(ON)} < 55 m\Omega @ V_{GS} = 4.5 V$  $R_{DS(ON)}$  < 85m $\Omega$ @  $V_{GS}$ =2.5V

**Application** 

Battery protection Load switch Uninterruptible power supply



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
BSS816NWH6327XTSA1	SOT-323	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	2	A
P <sub>D</sub>	Maximum Power Dissipation	0.3	W
Тл,Тэтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W

N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

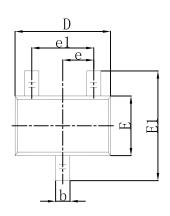
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250µA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =18V,V <sub>GS</sub> = 0V			1	μΑ
Gate-body leakage current	Igss	V <sub>GS</sub> =±12V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage (note2)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.7	1.0	V
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.0A			55	mΩ
Drain-source on-resistance (note2)		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.3A			85	mΩ
Maximum Continuous Drain to Source Diode Forward Current	Is				1.0	А
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V			1.2	V
DYNAMIC CHARACTERISTICS (note3)						
Input capacitance	C <sub>iss</sub>			300		pF
Output capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V, f =1MHz		120		pF
Reverse transfer capacitance	C <sub>rss</sub>	1 – 11011 12		80		pF
SWITCHING CHARACTERISTICS (no	te3)			,	•	
Turn-on delay time	t <sub>d(on)</sub>				15	nS
Turn-on rise time	t <sub>r</sub>	V <sub>GS</sub> =4.5V,V <sub>DS</sub> =10V,			85	nS
Turn-off delay time	t <sub>d(off)</sub>	$R_L$ =5.1 $\Omega$ , $R_G$ =5.1 $\Omega$			65	nS
Turn-off fall time	t <sub>f</sub>				27	nS

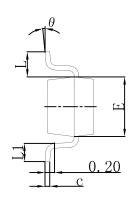
#### Notes:

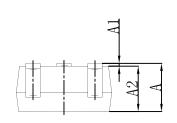
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test: Pulse Width=300µs, Duty Cycle=2%.
- 3. These parameters have no way to verify.



# **SOT-323 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	TYP	0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
K	0°	8°	0°	8°	

### BSS816NWH6327XTSA1

N-Channel Enhancement Mode MOSFET

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